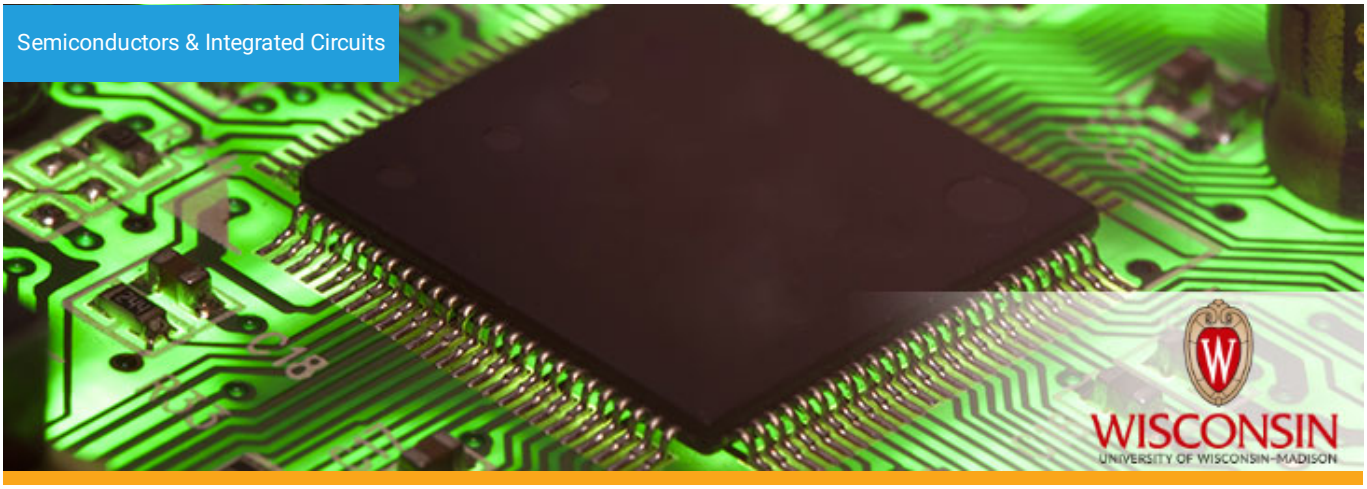

Group Iii-V Nitride-Based Ligth Emitting Devices Having Multilayered P-Type Contacts

View U.S. Patent No. 10,347,790 in PDF format.

WARF: P170282US02

Inventors: Zhenqiang Ma, Dong Liu

The Invention

Light-emitting devices having a multiple quantum well (MQW) pin diode structure are provided. The light-emitting devices include a multilayered p-type contact composed of a heavily p-type doped hole injection layer and a thin p-type group III-nitride layer. The materials of the hole injection layer and the p-type group III-nitride layer are separated by a layer of a material that allows current tunneling through the heterogeneous junction formed between the lattice mismatched materials.

Additional Information

For More Information About the Inventors

- Zhenqiang Ma

Tech Fields

- Semiconductors & Integrated Circuits : Design & fabrication

For current licensing status, please contact Jeanine Burmania at jeanine@warf.org or 608-960-9846